

# NTMFD4902NF

## Dual N-Channel Power MOSFET with Integrated Schottky

30 V, High Side 18 A / Low Side 23 A, Dual N-Channel SO8FL

### Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Low Side MOSFET with Integrated Schottky
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

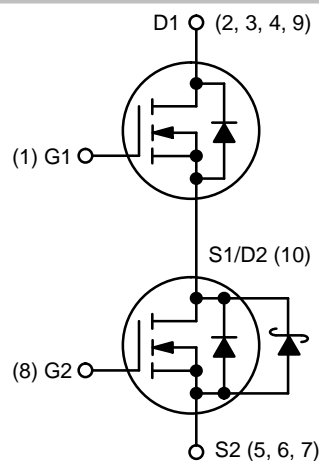
- DC-DC Converters
- System Voltage Rails
- Point of Load



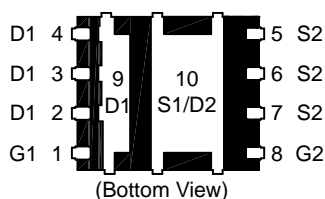
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

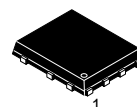
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
Q1 Top FET 30 V	6.5 m $\Omega$ @ 10 V	18 A
	10 m $\Omega$ @ 4.5 V	
Q2 Bottom FET 30 V	4.1 m $\Omega$ @ 10 V	23 A
	6.2 m $\Omega$ @ 4.5 V	



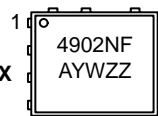
### PIN CONNECTIONS



### MARKING DIAGRAM



DFN8  
CASE 506BX



4902NF = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NTMFD4902NF

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter				Symbol	Value	Unit	
Drain-to-Source Voltage			Q1	V <sub>DSS</sub>	30	V	
Drain-to-Source Voltage			Q2				
Gate-to-Source Voltage			Q1	V <sub>GS</sub>	±20	V	
Gate-to-Source Voltage			Q2				
Continuous Drain Current R <sub>θJA</sub> (Note 1)	Steady State	T <sub>A</sub> = 25°C	Q1	I <sub>D</sub>	13.5	A	
		T <sub>A</sub> = 85°C			9.7		
		T <sub>A</sub> = 25°C	Q2		17.5		
		T <sub>A</sub> = 85°C			12.6		
Power Dissipation R <sub>θJA</sub> (Note 1)		T <sub>A</sub> = 25°C	Q1	P <sub>D</sub>	1.90	W	
			Q2		1.99		
Continuous Drain Current R <sub>θJA</sub> ≤ 10 s (Note 1)		T <sub>A</sub> = 25°C	Q1	I <sub>D</sub>	18.2	A	
			T <sub>A</sub> = 85°C				13.1
			T <sub>A</sub> = 25°C		Q2		23
			T <sub>A</sub> = 85°C				16.6
Power Dissipation R <sub>θJA</sub> ≤ 10 s (Note 1)		T <sub>A</sub> = 25°C	Q1	P <sub>D</sub>	3.45	W	
			Q2		3.45		
Continuous Drain Current R <sub>θJA</sub> (Note 2)		T <sub>A</sub> = 25°C	Q1	I <sub>D</sub>	10.3	A	
			T <sub>A</sub> = 85°C				7.4
			T <sub>A</sub> = 25°C		Q2		13.3
			T <sub>A</sub> = 85°C				9.6
Power Dissipation R <sub>θJA</sub> (Note 2)		T <sub>A</sub> = 25 °C	Q1	P <sub>D</sub>	1.10	W	
			Q2		1.16		
Pulsed Drain Current		TA = 25°C tp = 10 μs	Q1	I <sub>DM</sub>	60	A	
			Q2		80		
Operating Junction and Storage Temperature			Q1	T <sub>J</sub> , T <sub>STG</sub>	–55 to +150	°C	
			Q2				
Source Current (Body Diode)			Q1	I <sub>S</sub>	3.4	A	
			Q2		4.9		
Drain to Source dV/dt				dV/dt	6.0	V/ns	
Single Pulse Drain-to-Source Avalanche Energy (T <sub>J</sub> = 25C, V <sub>DD</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>L</sub> = XX A <sub>pk</sub> , L = 0.1 mH, R <sub>G</sub> = 25 Ω)		24 A	Q1	EAS	28.8	mJ	
		27 A	Q2	EAS	36.5		
Lead Temperature for Soldering Purposes (1/8” from case for 10 s)				T <sub>L</sub>	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm<sup>2</sup>.

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	FET	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 3)	Q1	$R_{\theta JA}$	65.9	°C/W
	Q2		62.8	
Junction-to-Ambient – Steady State (Note 4)	Q1	$R_{\theta JA}$	113.2	
	Q2		108	
Junction-to-Ambient – ( $t \leq 10$ s) (Note 3)	Q1	$R_{\theta JA}$	36.2	
	Q2		36.2	

3. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm<sup>2</sup>.

ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	FET	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS								
Drain-to-Source Break-down Voltage	Q1	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		30			V
	Q2		$V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$		30			
Drain-to-Source Break-down Voltage Temperature Coefficient	Q1	$V_{(BR)DSS} / T_J$				18		mV / °C
	Q2					15		
Zero Gate Voltage Drain Current	Q1	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$			1	$\mu\text{A}$
				$T_J = 125^\circ\text{C}$			10	
	Q2		$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$			500	
Gate-to-Source Leakage Current	Q1	$I_{GSS}$	$V_{GS} = 0\text{ V}, V_{DS} = \pm 20\text{ V}$				$\pm 100$	nA
	Q2						$\pm 100$	

## ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	Q1	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$		1.2		2.2	V
	Q2				1.2		2.2	
Negative Threshold Temperature Coefficient	Q1	$V_{GS(TH)} / T_J$				4.5		mV / °C
	Q2					4.0		
Drain-to-Source On Resistance	Q1	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$		5.2	6.5	mΩ
			$V_{GS} = 4.5\text{ V}$	$I_D = 10\text{ A}$		8.0	10	
	Q2		$V_{GS} = 10\text{ V}$	$I_D = 15\text{ A}$		3.3	4.1	
			$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}$		5.0	6.2	
Forward Transconductance	Q1	$g_{FS}$	$V_{DS} = 1.5\text{ V}, I_D = 10\text{ A}$			28		S
	Q2					35		

## CHARGES, CAPACITANCES &amp; GATE RESISTANCE

Input Capacitance	Q1	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 15 V		1150		pF
	Q2				1590		
Output Capacitance	Q1	C <sub>OSS</sub>			360		
	Q2				813		
Reverse Capacitance	Q1	C <sub>RSS</sub>			105		
	Q2				83		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

# NTMFD4902NF

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
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### CHARGES, CAPACITANCES & GATE RESISTANCE

Total Gate Charge	Q1	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 15 V; I <sub>D</sub> = 10 A		9.7		nC
	Q2				11.5		
Threshold Gate Charge	Q1	Q <sub>G(TH)</sub>			1.1		
	Q2				1.4		
Gate-to-Source Charge	Q1	Q <sub>GS</sub>			3.3		
	Q2				4.2		
Gate-to-Drain Charge	Q1	Q <sub>GD</sub>			3.7		
	Q2				3.4		
Total Gate Charge	Q1	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V; I <sub>D</sub> = 10 A		19.1		nC
	Q2				24.9		

### SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 10\text{ A}, R_G = 3.0\ \Omega$		9.0		ns
	Q2				10.5		
Rise Time	Q1	$t_r$			15		
	Q2				15.2		
Turn-Off Delay Time	Q1	$t_{d(OFF)}$			14		
	Q2				17.7		
Fall Time	Q1	$t_f$			4.0		
	Q2				4.7		

### SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 10\text{ A}, R_G = 3.0\text{ }\Omega$		6.0		ns
	Q2				7.0		
Rise Time	Q1	$t_r$			14		
	Q2				14		
Turn-Off Delay Time	Q1	$t_{d(OFF)}$			17		
	Q2				22		
Fall Time	Q1	$t_f$			3.0		
	Q2				3.3		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Voltage	Q1	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 3\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.75	1.0	V
				$T_J = 125^{\circ}\text{C}$		0.62		
	Q2		$V_{GS} = 0\text{ V},$ $I_S = 2\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.37	0.70	
				$T_J = 125^{\circ}\text{C}$		0.31		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

# NTMFD4902NF

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN–SOURCE DIODE CHARACTERISTICS							
Reverse Recovery Time	Q1	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 3\text{ A}$		23		ns
	Q2				24.5		
Charge Time	Q1	$t_a$			12		
	Q2				13		
Discharge Time	Q1	$t_b$			11		
	Q2				11.5		
Reverse Recovery Charge	Q1	$Q_{RR}$			12		nC
	Q2				24		

## PACKAGE PARASITIC VALUES

Source Inductance	Q1	L <sub>S</sub>	T <sub>A</sub> = 25°C		0.38		nH
	Q2				0.65		
Drain Inductance	Q1	L <sub>D</sub>			0.054		nH
	Q2				0.007		
Gate Inductance	Q1	L <sub>G</sub>			1.5		nH
	Q2				1.5		
Gate Resistance	Q1	R <sub>G</sub>			0.8		Ω
	Q2				0.8		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTMFD4902NFT1G	DFN8 (Pb-Free)	1500 / Tape & Reel
NTMFD4902NFT3G	DFN8 (Pb-Free)	5000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS – Q1

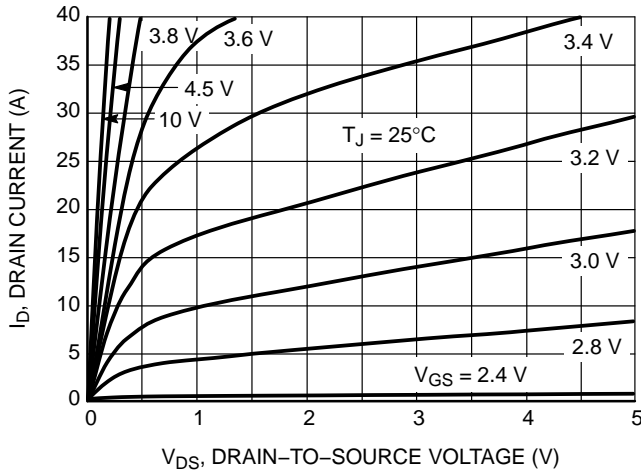


Figure 1. On-Region Characteristics

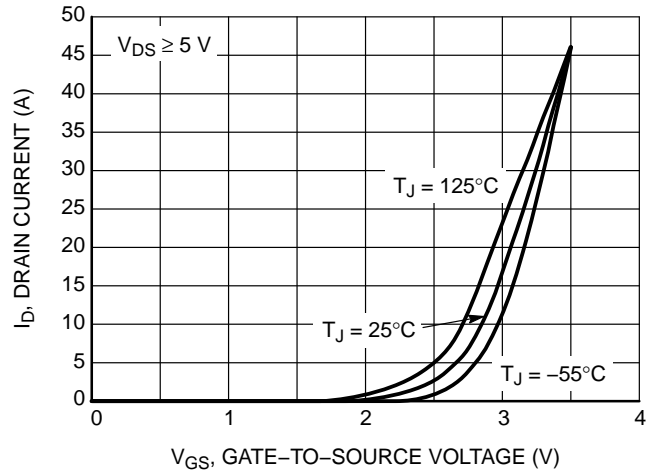


Figure 2. Transfer Characteristics

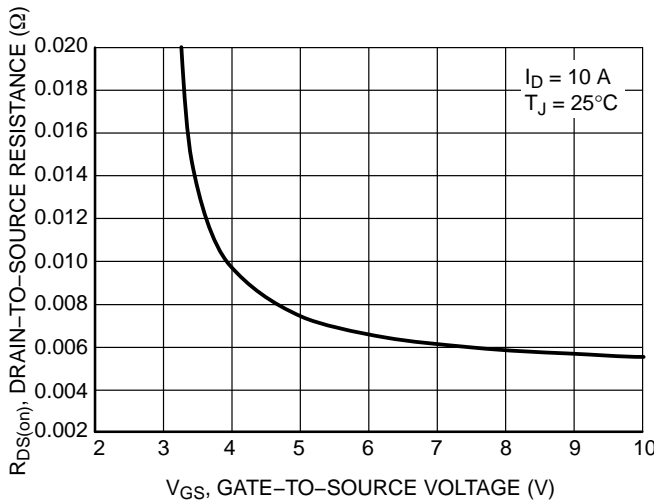


Figure 3. On-Resistance vs. Gate-to-Source Resistance

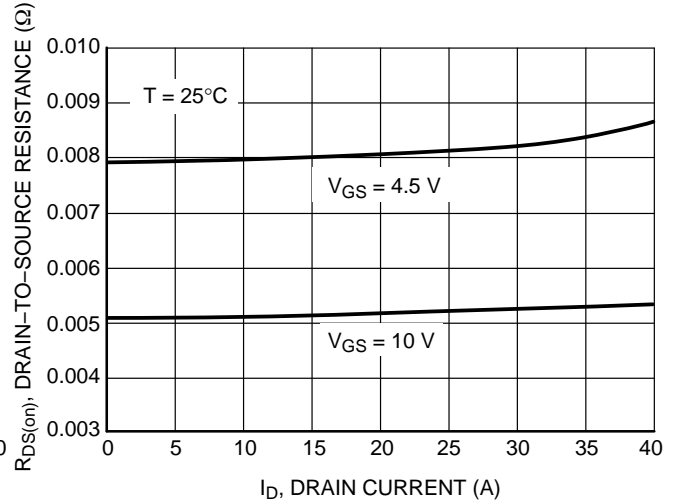


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

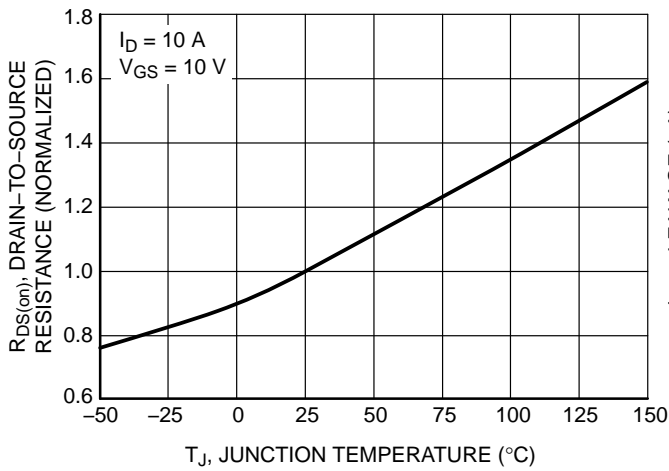


Figure 5. On-Resistance Variation with Temperature

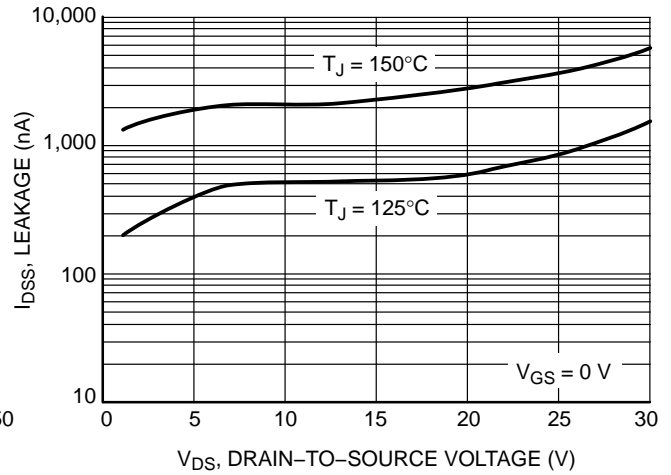


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – Q1

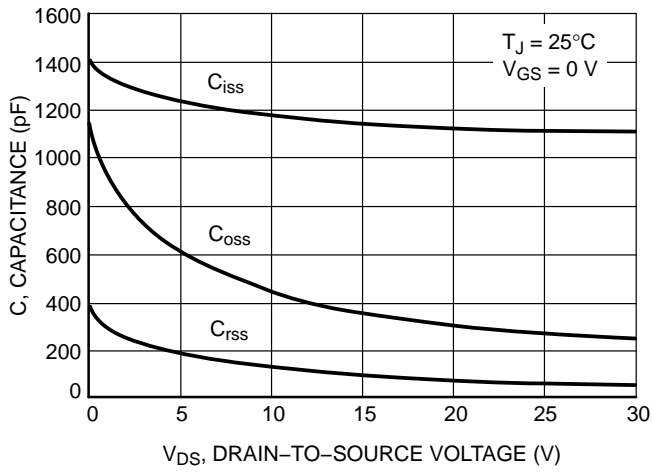


Figure 7. Capacitance Variation

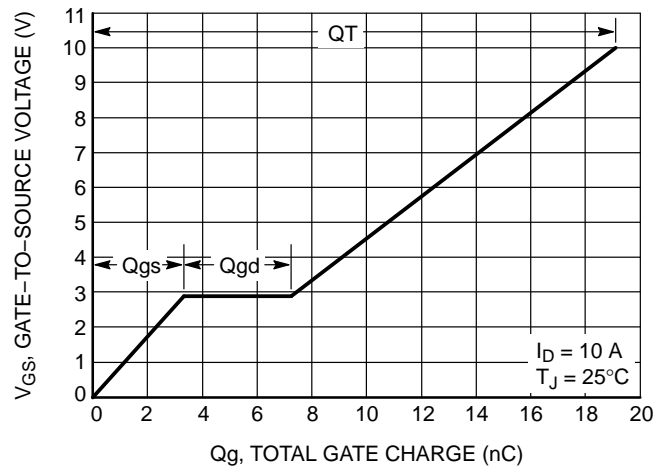


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

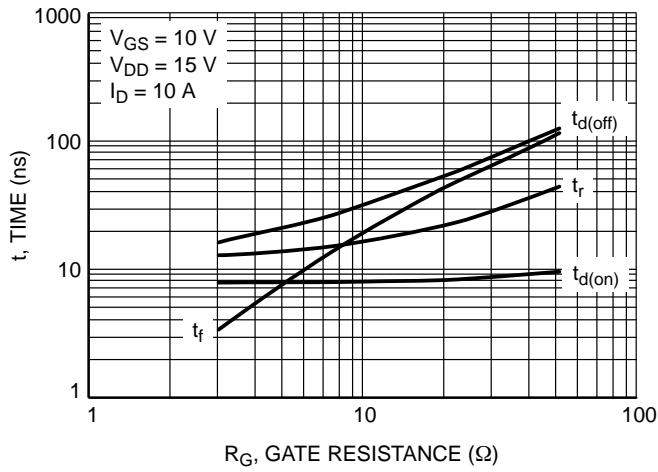


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

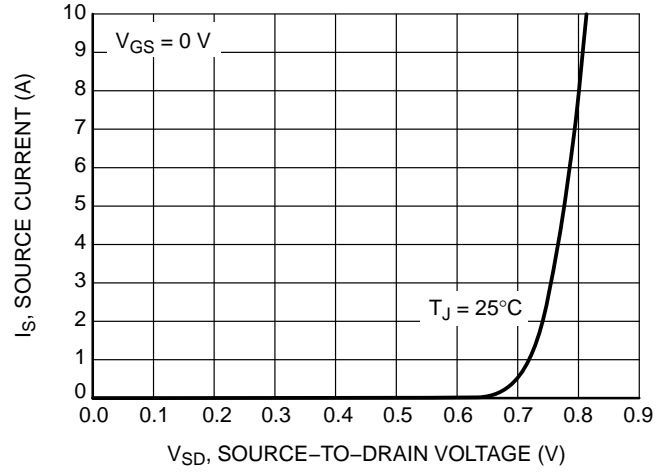


Figure 10. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS – Q2

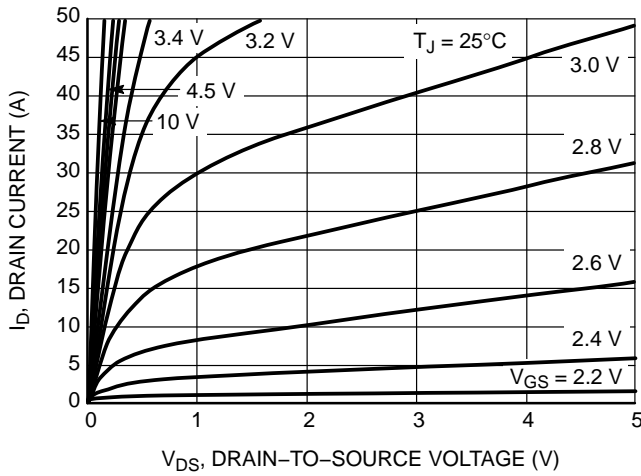


Figure 11. On-Region Characteristics

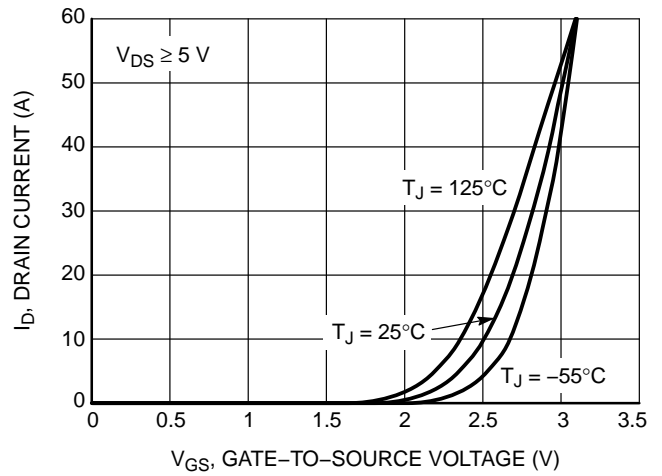


Figure 12. Transfer Characteristics

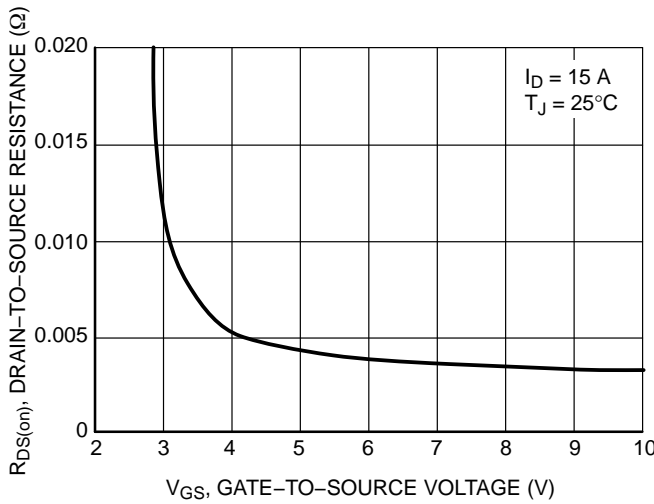


Figure 13. On-Resistance vs. Gate-to-Source Resistance

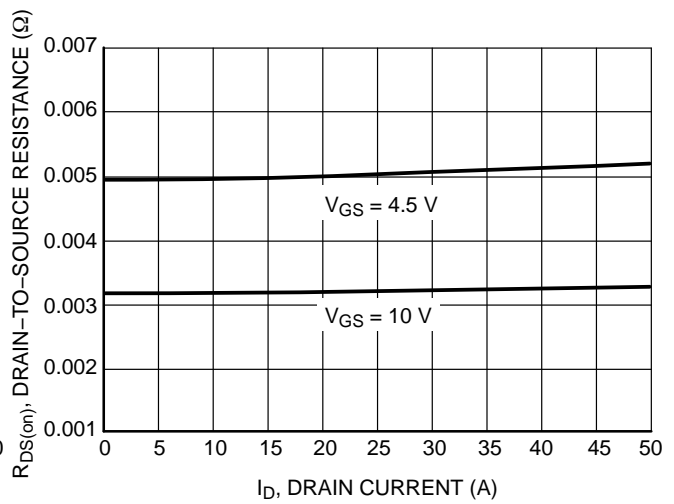


Figure 14. On-Resistance vs. Drain Current and Gate Voltage

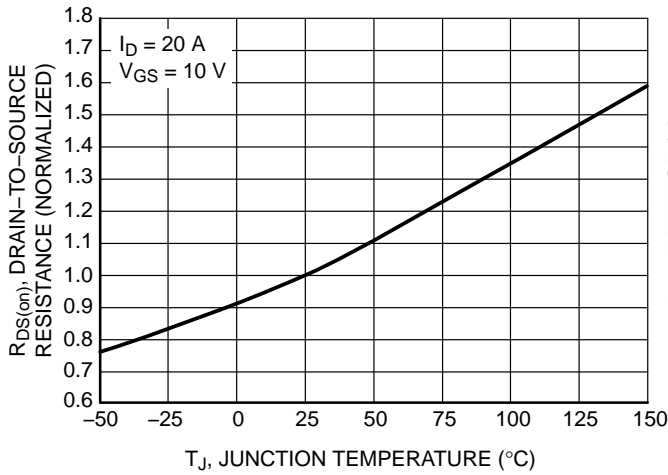


Figure 15. On-Resistance Variation with Temperature

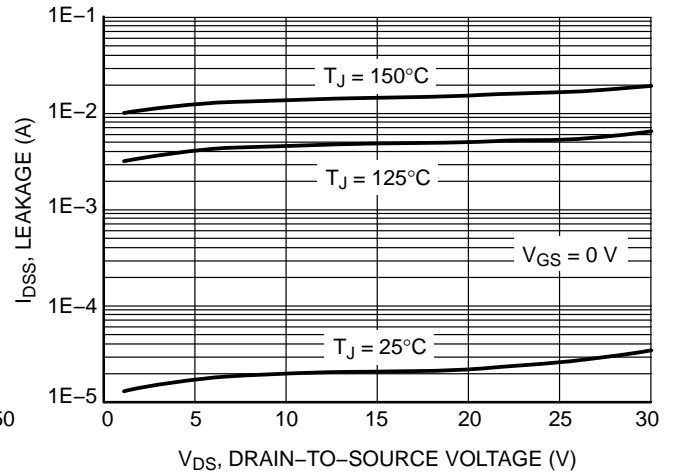


Figure 16. Drain-to-Source Leakage Current vs. Voltage



TYPICAL CHARACTERISTICS – Q2

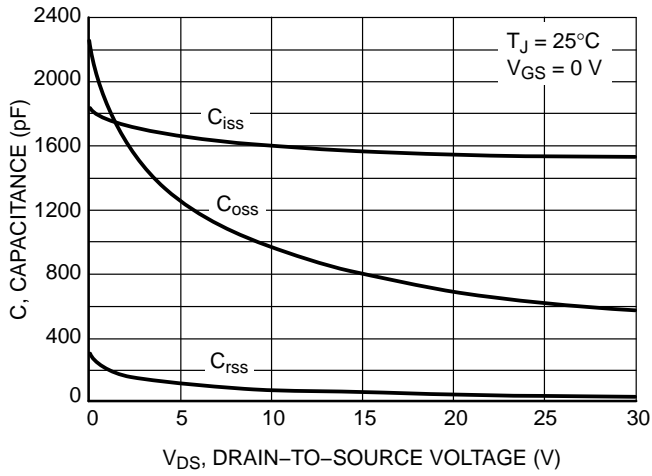


Figure 17. Capacitance Variation

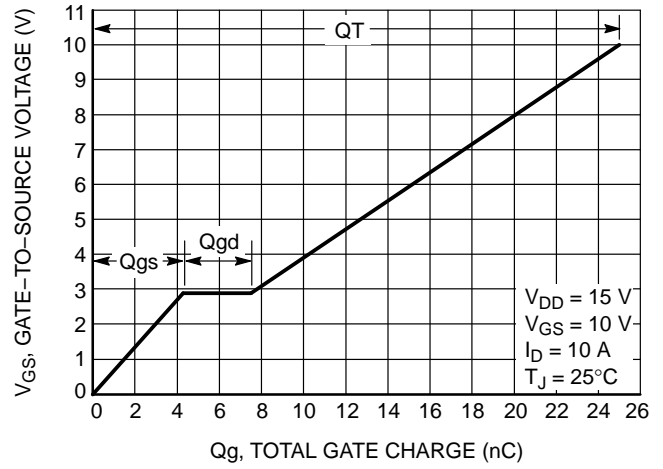


Figure 18. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

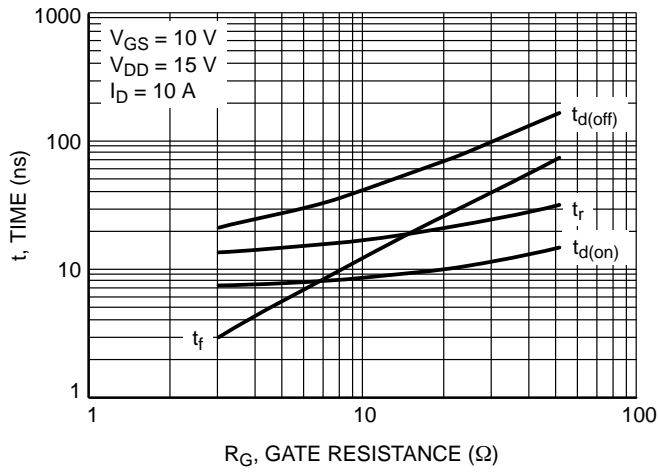


Figure 19. Resistive Switching Time Variation vs. Gate Resistance

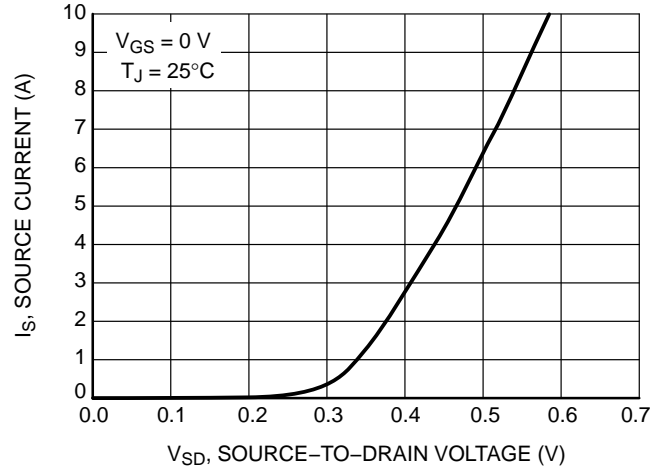
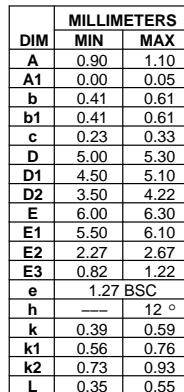


Figure 20. Diode Forward Voltage vs. Current

## PACKAGE DIMENSIONS

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
5. DIMENSIONS b AND L ARE MEASURED AT THE PACKAGE SURFACE
6. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
7. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



5.35

8X 0.64

8X 0.69

PACKAGE OUTLINE

6.45

1.97

2.33

2.68


1.27 PITCH

1.22

4X 0.69

DIMENSION: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, [SOLDDRRM/D](#).

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